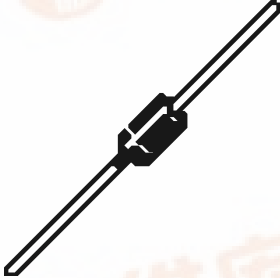




Data Sheet

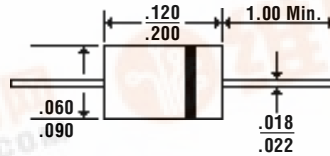
500 mW EPITAXIAL PLANAR DIODES

Description



Mechanical Dimensions

JEDEC
DO-35



FBAV19...21 Series

Features

- PLANAR PROCESS
- 500 mW POWER DISSIPATION
- INDUSTRY STANDARD DO-35 PACKAGE
- MEETS UL SPECIFICATION 94V-0

FBAV19...21 Series				Units
Maximum Ratings	FBAV19	FBAV20	FBAV21	
Peak Reverse Voltage... V_{RM}	120	200	250	Volts
RMS Reverse Voltage... $V_{R(rms)}$	100	150	200	Volts
Average Forward Rectified Current... I_O	250			mAmps
Non-Repetitive Peak Forward Surge Current... I_{FSM}	500			mAmps
Power Dissipation... P_D	500			mW
Operating Temperature Range... T_J	-25 to 85			°C
Storage Temperature Range... T_{STRG}	-65 to 200			°C
Electrical Characteristics				
Maximum Forward Voltage... V_F @ $I_F = 100$ mA	1.0			Volts
Maximum DC Reverse Current... I_R @ Rated V_R	0.1			μAmps
Dynamic Forward Resistance... R_F	5.0			Ω
Maximum Diode Capacitance... C_D	5.0			pF
Typical Thermal Resistance... $R_{θJA}$	.35			K / mW
Maximum Reverse Recovery Time... t_{RR}	50			ns

Device Under Test

